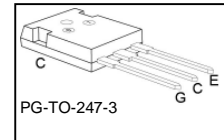
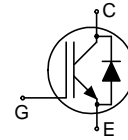


## Fast IGBT in NPT-technology with soft, fast recovery anti-parallel Emitter Controlled Diode

- 40% lower  $E_{off}$  compared to previous generation
- Short circuit withstand time – 10  $\mu$ s
- Designed for:
  - Motor controls
  - Inverter
  - SMPS
- NPT-Technology offers:
  - very tight parameter distribution
  - high ruggedness, temperature stable behaviour
  - parallel switching capability
- Pb-free lead plating; RoHS compliant
- Qualified according to JEDEC<sup>1</sup> for target applications
- Complete product spectrum and PSpice Models : <http://www.infineon.com/igbt/>



Type	$V_{CE}$	$I_C$	$E_{off}$	$T_j$	Marking	Package
SKW25N120	1200V	25A	2.9mJ	150°C	K25N120	PG-TO-247-3

### Maximum Ratings

Parameter	Symbol	Value	Unit
Collector-emitter voltage	$V_{CE}$	1200	V
DC collector current	$I_C$		A
$T_C = 25^\circ\text{C}$		46	
$T_C = 100^\circ\text{C}$		25	
Pulsed collector current, $t_p$ limited by $T_{jmax}$	$I_{Cpuls}$	84	
Turn off safe operating area $V_{CE} \leq 1200\text{V}, T_j \leq 150^\circ\text{C}$	-	84	
Diode forward current	$I_F$		
$T_C = 25^\circ\text{C}$		42	
$T_C = 100^\circ\text{C}$		25	
Diode pulsed current, $t_p$ limited by $T_{jmax}$	$I_{Fpuls}$	80	
Gate-emitter voltage	$V_{GE}$	$\pm 20$	V
Short circuit withstand time <sup>2</sup> $V_{GE} = 15\text{V}, 100\text{V} \leq V_{CC} \leq 1200\text{V}, T_j \leq 150^\circ\text{C}$	$t_{SC}$	10	$\mu$ s
Power dissipation $T_C = 25^\circ\text{C}$	$P_{tot}$	313	W
Operating junction and storage temperature	$T_j, T_{stg}$	-55...+150	°C
Soldering temperature, wavesoldering, 1.6mm (0.063 in.) from case for 10s	$T_s$	260	

<sup>1</sup> J-STD-020 and JESD-022

<sup>2</sup> Allowed number of short circuits: <1000; time between short circuits: >1s.

**Thermal Resistance**

Parameter	Symbol	Conditions	Max. Value	Unit
<b>Characteristic</b>				
IGBT thermal resistance, junction – case	$R_{thJC}$		0.4	K/W
Diode thermal resistance, junction – case	$R_{thJCD}$		1.15	
Thermal resistance, junction – ambient	$R_{thJA}$		40	

**Electrical Characteristic, at  $T_j = 25\text{ }^\circ\text{C}$ , unless otherwise specified**

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
<b>Static Characteristic</b>						
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V,$ $I_C=1500\mu A$	1200	-	-	V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE} = 15V, I_C=25A$ $T_j=25^\circ C$ $T_j=150^\circ C$	2.5 -	3.1 3.7	3.6 4.3	
Diode forward voltage	$V_F$	$V_{GE}=0V, I_F=25A$ $T_j=25^\circ C$ $T_j=150^\circ C$	-	2.0 1.75	2.5	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=1000\mu A,$ $V_{CE}=V_{GE}$	3	4	5	
Zero gate voltage collector current	$I_{CES}$	$V_{CE}=1200V, V_{GE}=0V$ $T_j=25^\circ C$ $T_j=150^\circ C$	- -	- -	350 1400	$\mu A$
Gate-emitter leakage current	$I_{GES}$	$V_{CE}=0V, V_{GE}=20V$	-	-	100	nA
Transconductance	$g_{fs}$	$V_{CE}=20V, I_C=25A$	-	20	-	S
<b>Dynamic Characteristic</b>						
Input capacitance	$C_{iss}$	$V_{CE}=25V,$ $V_{GE}=0V,$ $f=1MHz$	-	2150	2600	pF
Output capacitance	$C_{oss}$		-	260	310	
Reverse transfer capacitance	$C_{riss}$		-	110	130	
Gate charge	$Q_{Gate}$	$V_{CC}=960V, I_C=25A$ $V_{GE}=15V$	-	225	300	nC
Internal emitter inductance Measured 5mm (0.197 in.) from case	$L_E$		-	13	-	nH
Short circuit collector current <sup>1)</sup>	$I_{C(SC)}$	$V_{GE}=15V, t_{SC}\leq 10\mu s$ $100V\leq V_{CC}\leq 1200V,$ $T_j\leq 150^\circ C$	-	240	-	A

<sup>1)</sup> Allowed number of short circuits: <1000; time between short circuits: >1s

**Switching Characteristic, Inductive Load, at  $T_j=25\text{ }^\circ\text{C}$** 

Parameter	Symbol	Conditions	Value			Unit
			Min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=25\text{ }^\circ\text{C}$ , $V_{CC}=800\text{V}$ , $I_C=25\text{A}$ , $V_{GE}=15/0\text{V}$ , $R_G=22\Omega$ , $L_{\sigma}^{1)}=180\text{nH}$ , $C_{\sigma}^{1)}=40\text{pF}$ Energy losses include "tail" and diode reverse recovery.	-	45	60	ns
Rise time	$t_r$		-	40	52	
Turn-off delay time	$t_{d(off)}$		-	730	950	
Fall time	$t_f$		-	30	39	
Turn-on energy	$E_{on}$		-	2.2	2.9	mJ
Turn-off energy	$E_{off}$		-	1.5	2.0	
Total switching energy	$E_{ts}$		-	3.7	4.9	

**Anti-Parallel Diode Characteristic**

Diode reverse recovery time	$t_{rr}$	$T_j=25\text{ }^\circ\text{C}$ , $V_R=800\text{V}$ , $I_F=25\text{A}$ , $di_F/dt=650\text{A}/\mu\text{s}$	-	90		ns
	$t_S$		-			
	$t_F$		-			
Diode reverse recovery charge	$Q_{rr}$		-	1.0		$\mu\text{C}$
Diode peak reverse recovery current	$I_{rrm}$		-	20		A
Diode peak rate of fall of reverse recovery current during $t_F$	$di_{rr}/dt$	-	470		$\text{A}/\mu\text{s}$	

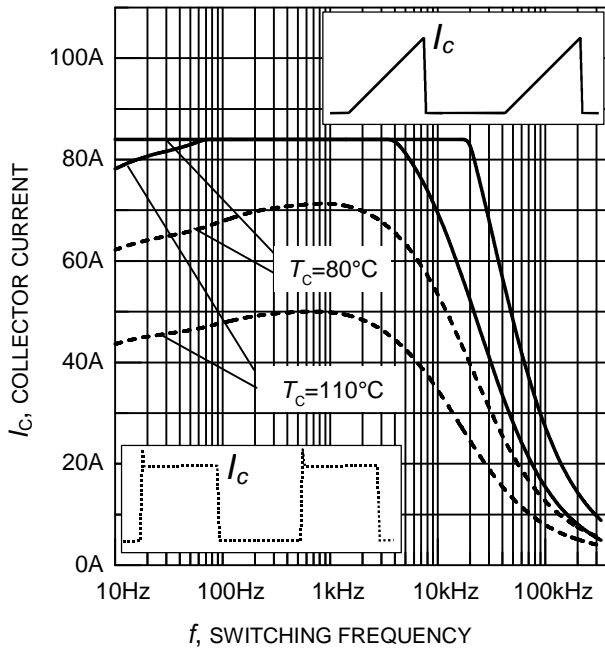
**Switching Characteristic, Inductive Load, at  $T_j=150\text{ }^\circ\text{C}$** 

Parameter	Symbol	Conditions	Value			Unit
			Min.	typ.	max.	
<b>IGBT Characteristic</b>						
Turn-on delay time	$t_{d(on)}$	$T_j=150\text{ }^\circ\text{C}$ $V_{CC}=800\text{V}$ , $I_C=25\text{A}$ , $V_{GE}=15/0\text{V}$ , $R_G=22\Omega$ , $L_{\sigma}^{1)}=180\text{nH}$ , $C_{\sigma}^{1)}=40\text{pF}$ Energy losses include "tail" and diode reverse recovery.	-	50	60	ns
Rise time	$t_r$		-	36	43	
Turn-off delay time	$t_{d(off)}$		-	820	990	
Fall time	$t_f$		-	42	50	
Turn-on energy	$E_{on}$		-	3.8	4.6	mJ
Turn-off energy	$E_{off}$		-	2.9	3.8	
Total switching energy	$E_{ts}$		-	6.7	8.4	

**Anti-Parallel Diode Characteristic**

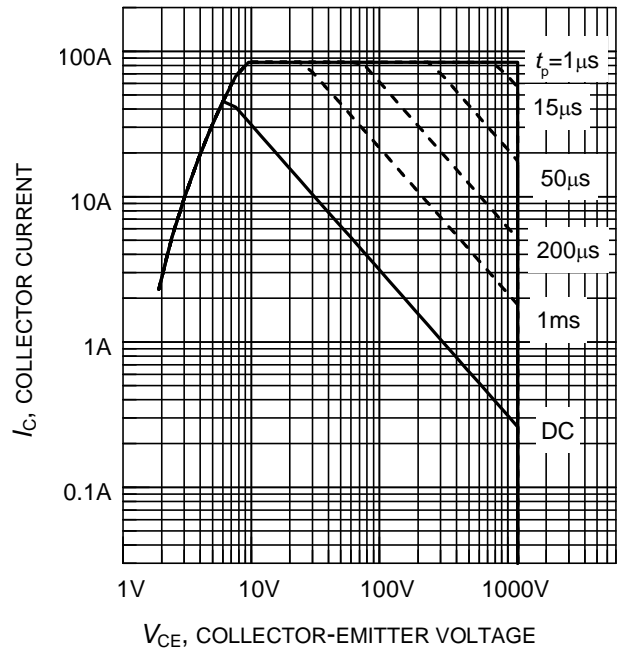
Diode reverse recovery time	$t_{rr}$	$T_j=150\text{ }^\circ\text{C}$ $V_R=800\text{V}$ , $I_F=25\text{A}$ , $di_F/dt=750\text{A}/\mu\text{s}$	-	280		ns
	$t_S$		-			
	$t_F$		-			
Diode reverse recovery charge	$Q_{rr}$		-	4.3		$\mu\text{C}$
Diode peak reverse recovery current	$I_{rrm}$		-	32		A
Diode peak rate of fall of reverse recovery current during $t_F$	$di_{rr}/dt$	-	130		$\text{A}/\mu\text{s}$	

<sup>1)</sup> Leakage inductance  $L_{\sigma}$  and stray capacity  $C_{\sigma}$  due to dynamic test circuit in figure E.



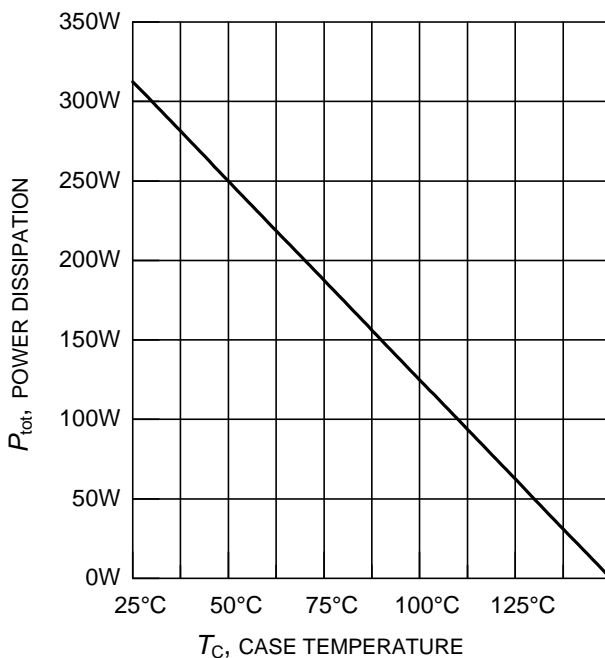
**Figure 1. Collector current as a function of switching frequency**

( $T_j \leq 150^\circ\text{C}$ ,  $D = 0.5$ ,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $R_G = 22\Omega$ )



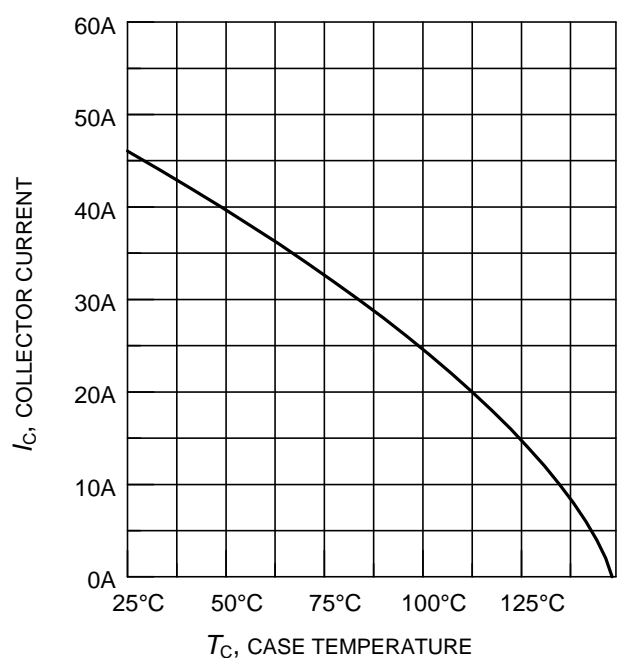
**Figure 2. Safe operating area**

( $D = 0$ ,  $T_C = 25^\circ\text{C}$ ,  $T_j \leq 150^\circ\text{C}$ )



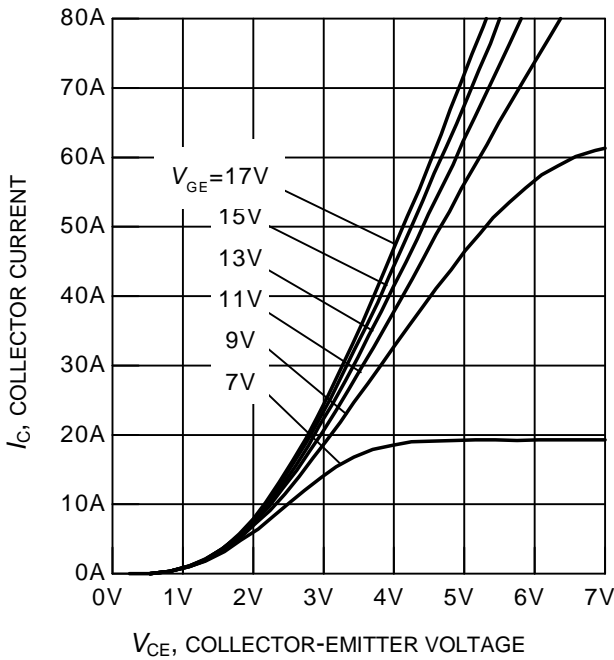
**Figure 3. Power dissipation as a function of case temperature**

( $T_j \leq 150^\circ\text{C}$ )

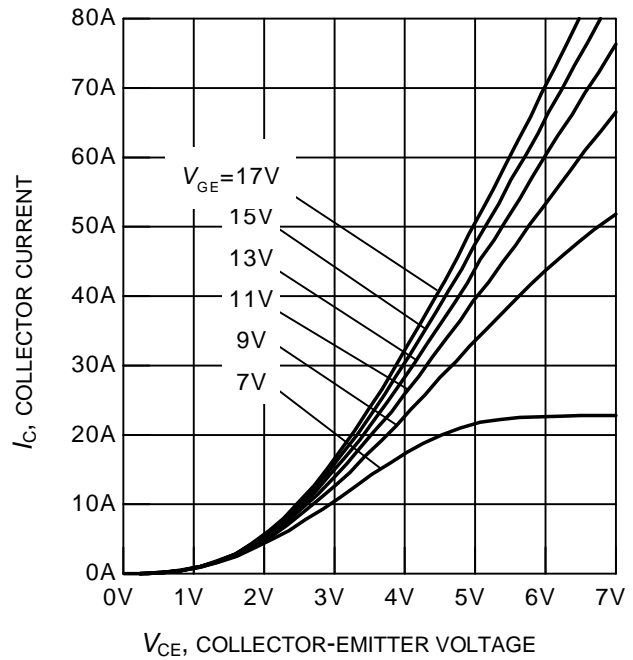


**Figure 4. Collector current as a function of case temperature**

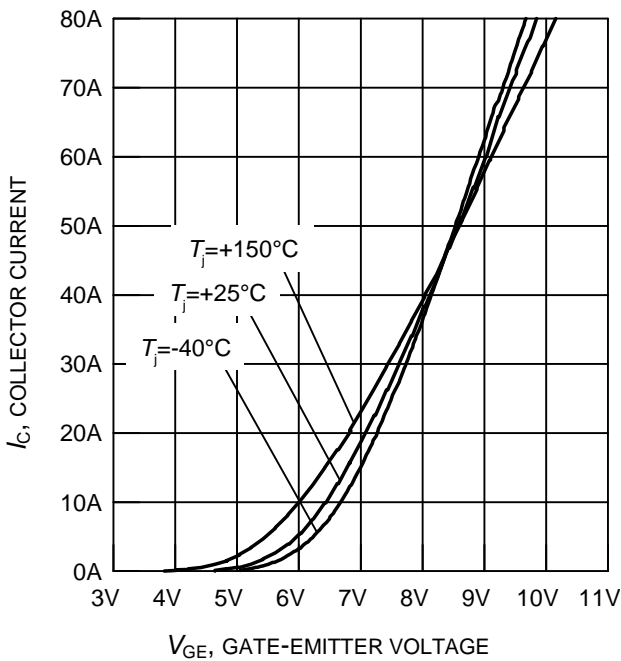
( $V_{GE} \leq 15\text{V}$ ,  $T_j \leq 150^\circ\text{C}$ )



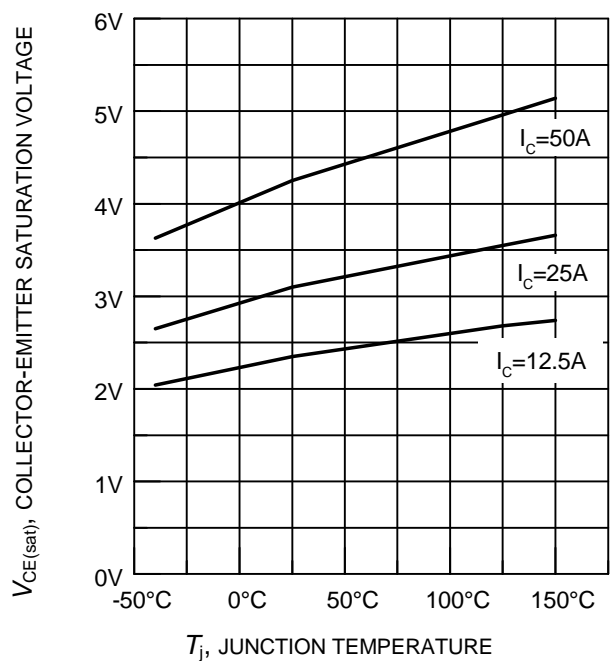
**Figure 5. Typical output characteristics**  
( $T_j = 25^\circ\text{C}$ )



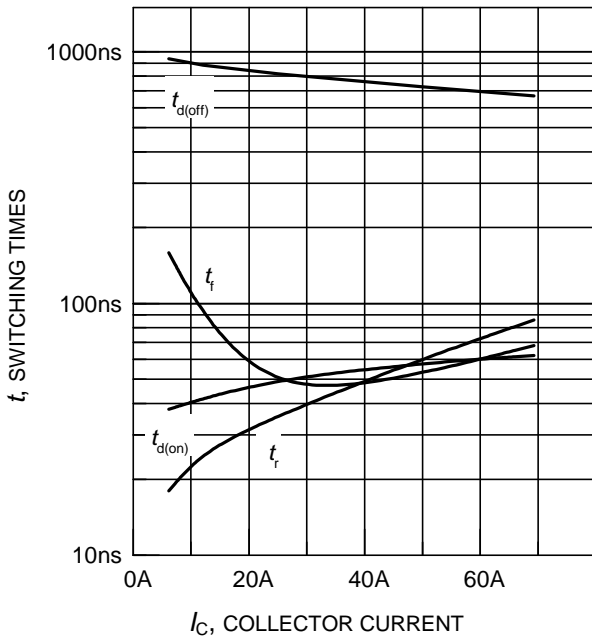
**Figure 6. Typical output characteristics**  
( $T_j = 150^\circ\text{C}$ )



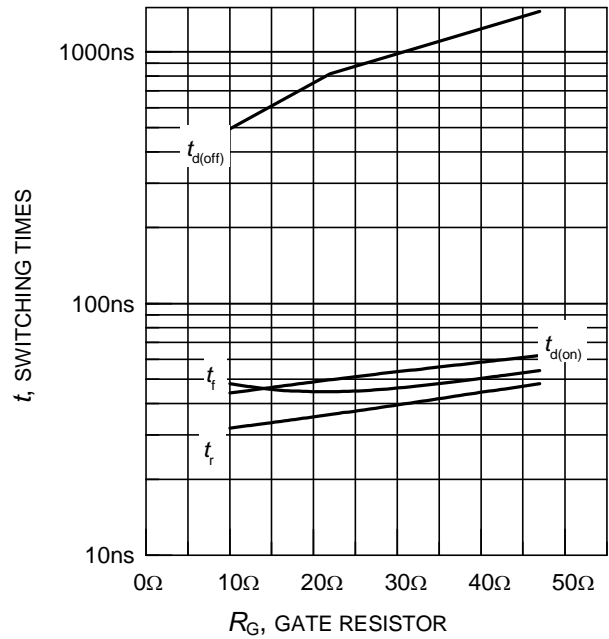
**Figure 7. Typical transfer characteristics**  
( $V_{CE} = 20\text{V}$ )



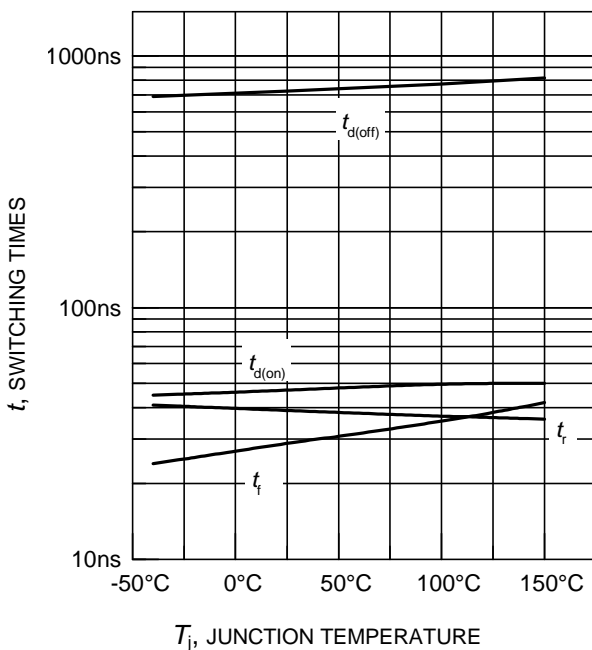
**Figure 8. Typical collector-emitter saturation voltage as a function of junction temperature**  
( $V_{GE} = 15\text{V}$ )



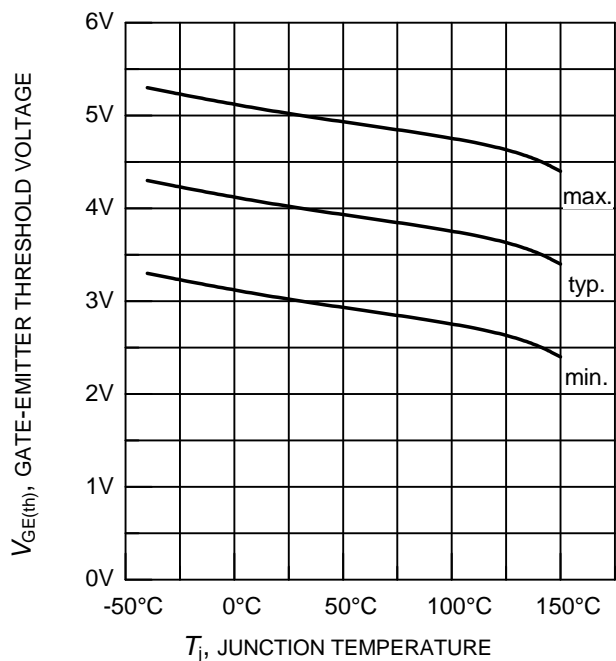
**Figure 9. Typical switching times as a function of collector current**  
 (inductive load,  $T_j = 150^\circ\text{C}$ ,  
 $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $R_G = 22\Omega$ ,  
 dynamic test circuit in Fig.E )



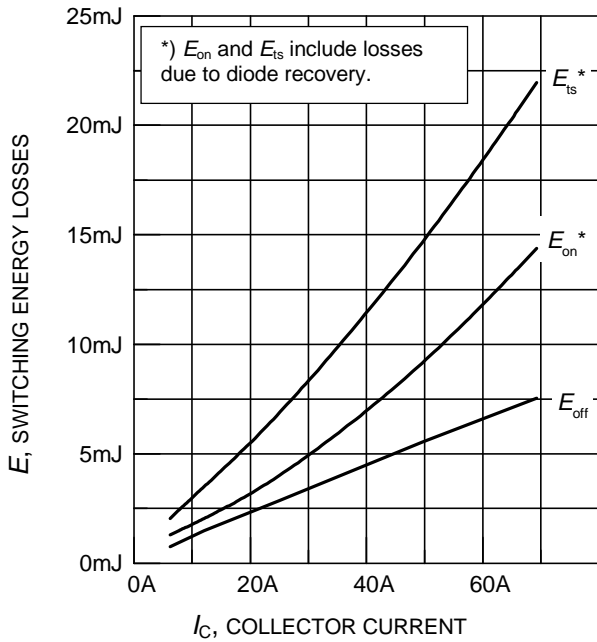
**Figure 10. Typical switching times as a function of gate resistor**  
 (inductive load,  $T_j = 150^\circ\text{C}$ ,  
 $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 25\text{A}$ ,  
 dynamic test circuit in Fig.E )



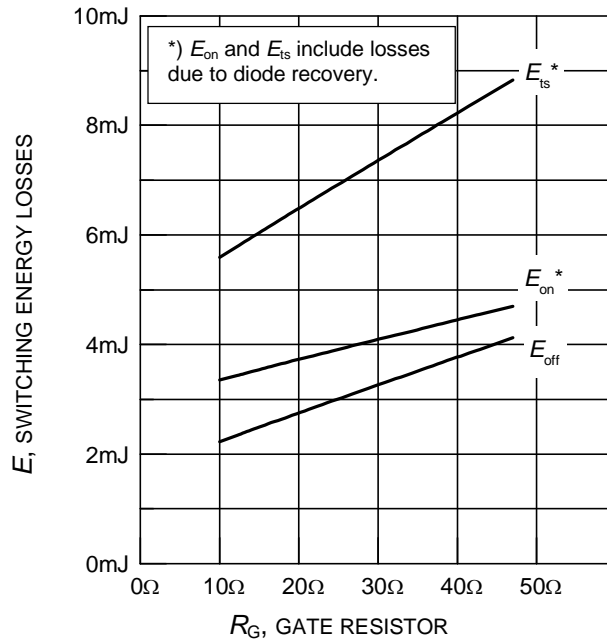
**Figure 11. Typical switching times as a function of junction temperature**  
 (inductive load,  $V_{CE} = 800\text{V}$ ,  
 $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 25\text{A}$ ,  $R_G = 22\Omega$ ,  
 dynamic test circuit in Fig.E )



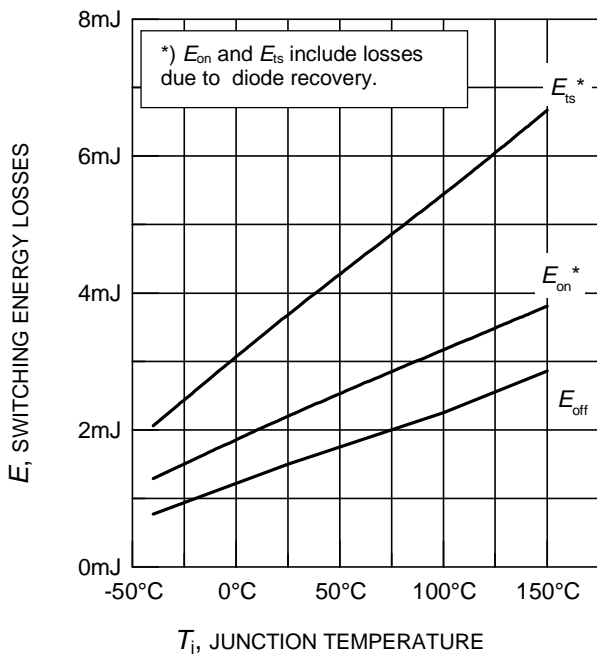
**Figure 12. Gate-emitter threshold voltage as a function of junction temperature**  
 ( $I_C = 0.3\text{mA}$ )



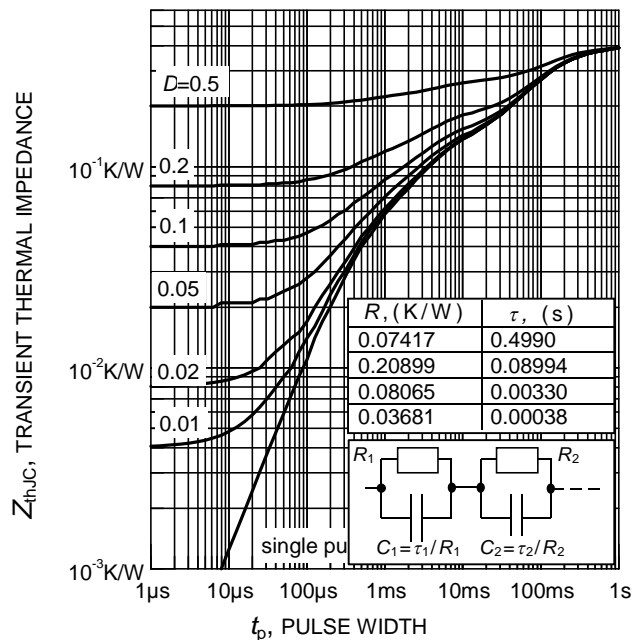
**Figure 13. Typical switching energy losses as a function of collector current** (inductive load,  $T_j = 150^\circ\text{C}$ ,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $R_G = 22\Omega$ , dynamic test circuit in Fig.E )



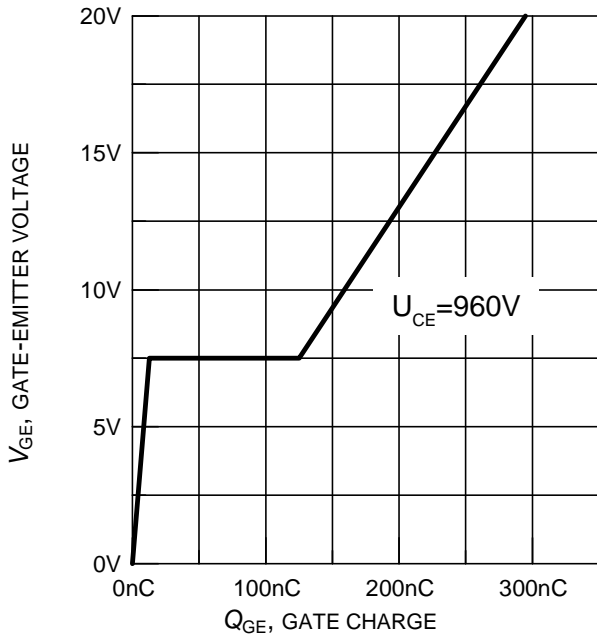
**Figure 14. Typical switching energy losses as a function of gate resistor** (inductive load,  $T_j = 150^\circ\text{C}$ ,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 25\text{A}$ , dynamic test circuit in Fig.E )



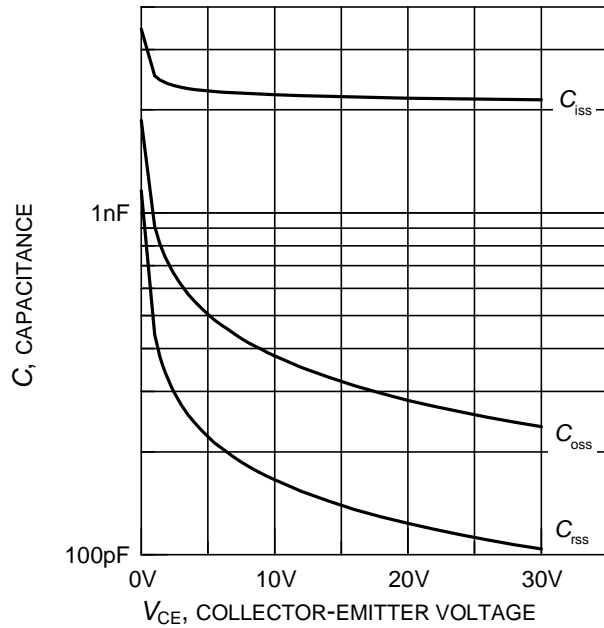
**Figure 15. Typical switching energy losses as a function of junction temperature** (inductive load,  $V_{CE} = 800\text{V}$ ,  $V_{GE} = +15\text{V}/0\text{V}$ ,  $I_C = 25\text{A}$ ,  $R_G = 22\Omega$ , dynamic test circuit in Fig.E )



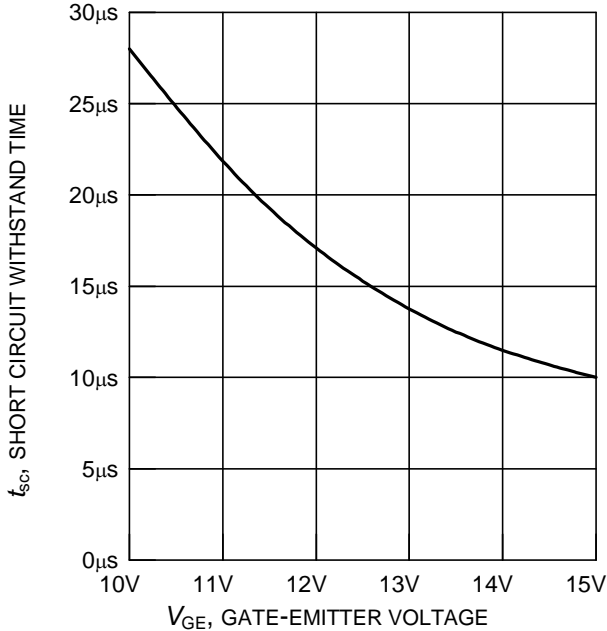
**Figure 16. IGBT transient thermal impedance as a function of pulse width** ( $D = t_p / T$ )



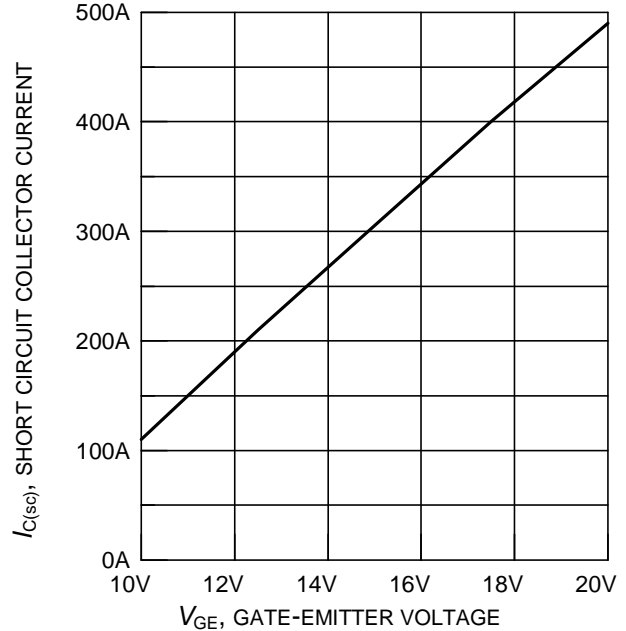
**Figure 17. Typical gate charge**  
( $I_C = 25A$ )



**Figure 18. Typical capacitance as a function of collector-emitter voltage**  
( $V_{GE} = 0V, f = 1MHz$ )

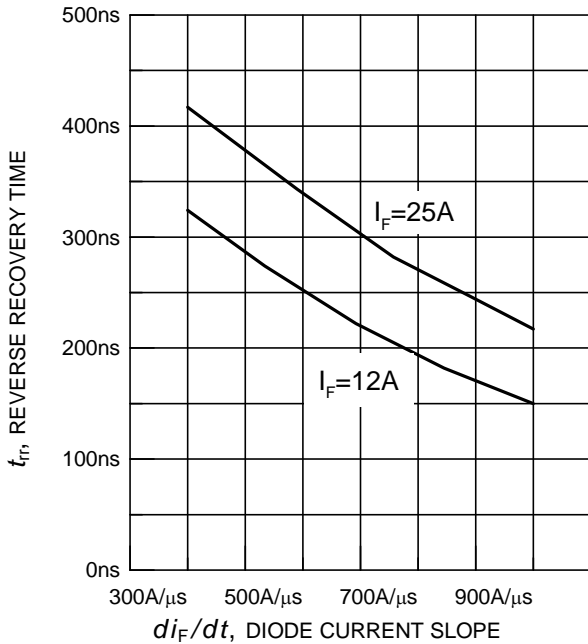


**Figure 19. Short circuit withstand time as a function of gate-emitter voltage**  
( $V_{CE} = 1200V, \text{start at } T_j = 25^\circ C$ )

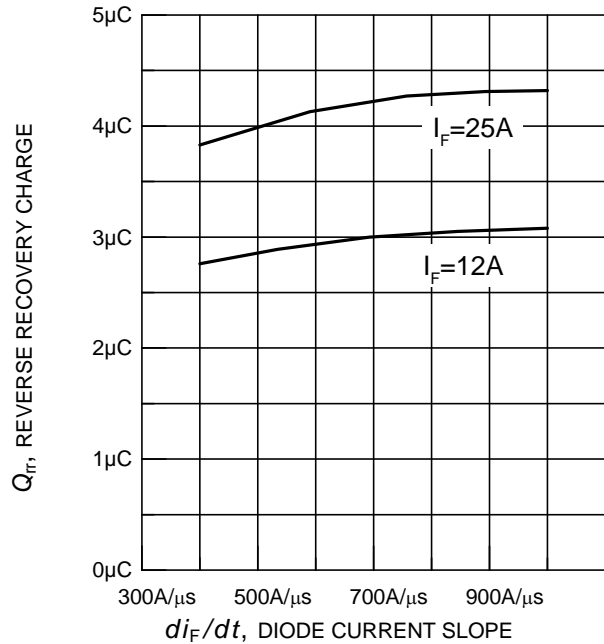


**Figure 20. Typical short circuit collector current as a function of gate-emitter voltage**  
( $100V \leq V_{CE} \leq 1200V, T_C = 25^\circ C, T_j \leq 150^\circ C$ )

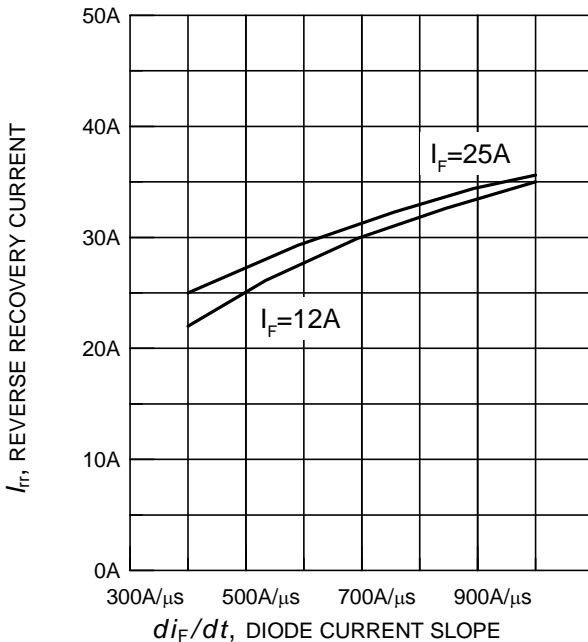




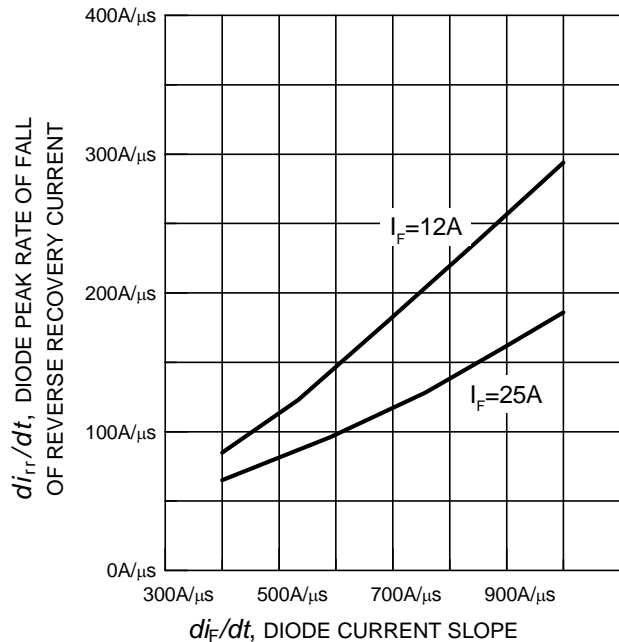
**Figure 21. Typical reverse recovery time as a function of diode current slope**  
 ( $V_R = 800V$ ,  $T_j = 150^\circ C$ ,  
 dynamic test circuit in Fig.E )



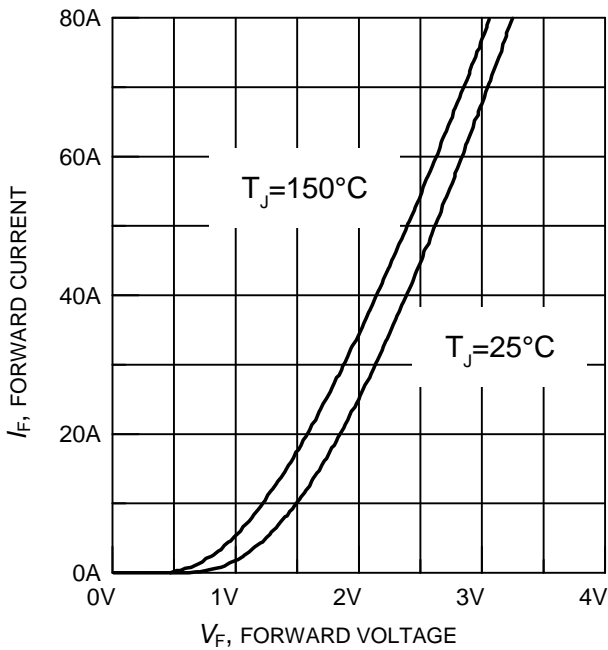
**Figure 22. Typical reverse recovery charge as a function of diode current slope**  
 ( $V_R = 800V$ ,  $T_j = 150^\circ C$ ,  
 dynamic test circuit in Fig.E )



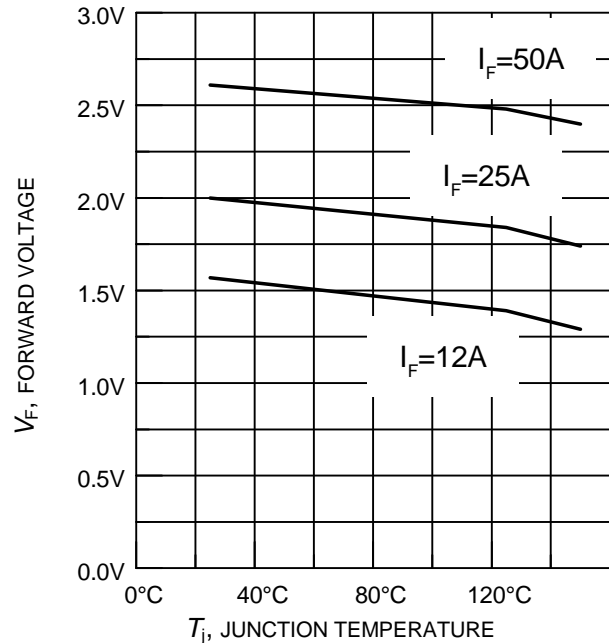
**Figure 23. Typical reverse recovery current as a function of diode current slope**  
 ( $V_R = 800V$ ,  $T_j = 150^\circ C$ ,  
 dynamic test circuit in Fig.E )



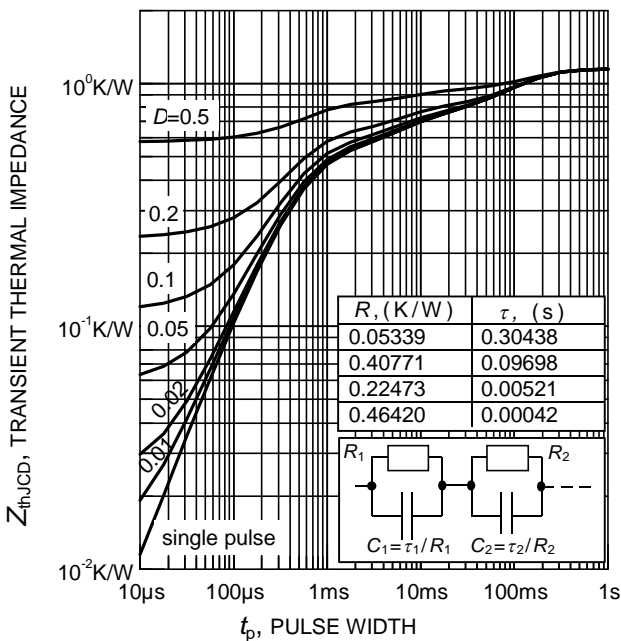
**Figure 24. Typical diode peak rate of fall of reverse recovery current as a function of diode current slope**  
 ( $V_R = 800V$ ,  $T_j = 150^\circ C$ ,  
 dynamic test circuit in Fig.E )



**Figure 25. Typical diode forward current as a function of forward voltage**

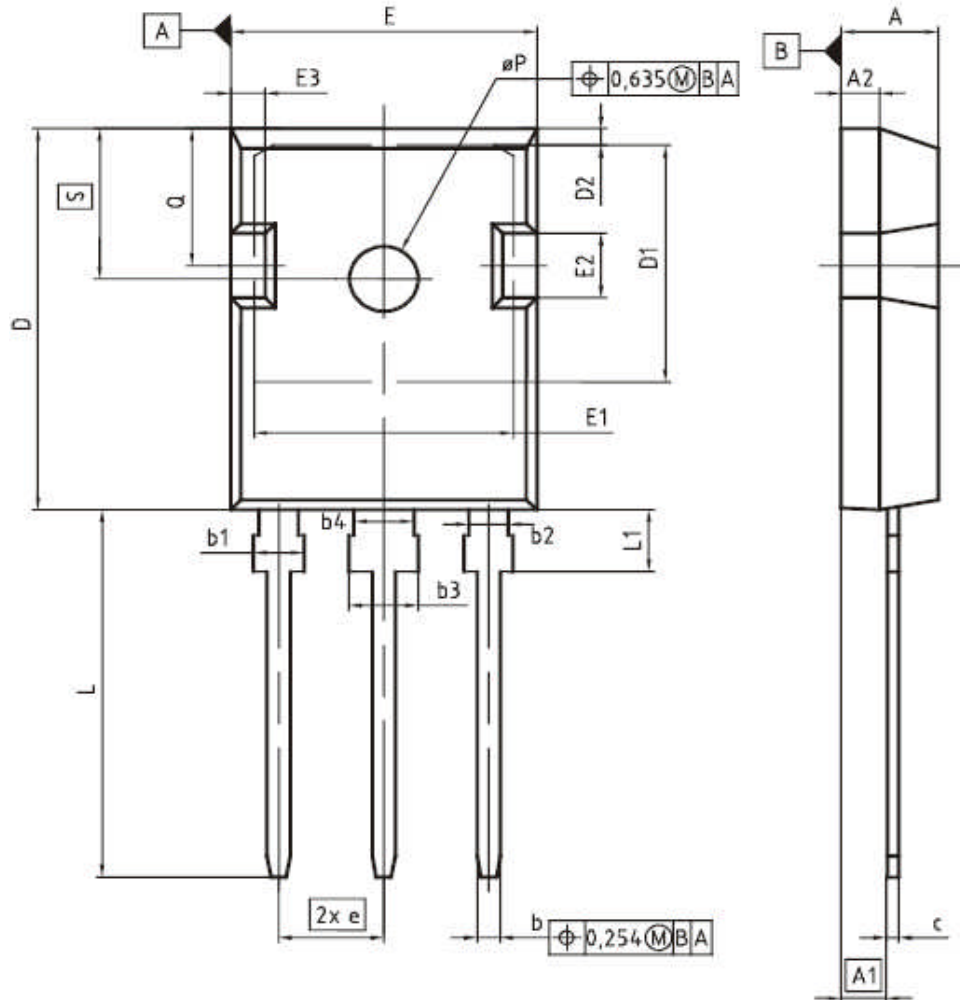


**Figure 26. Typical diode forward voltage as a function of junction temperature**



**Figure 27. Diode transient thermal impedance as a function of pulse width ( $D = t_p / T$ )**

PG-TO247-3



DIM	MILLIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	4,83	5,21	0,190	0,205
A1	2,27	2,54	0,089	0,100
A2	1,85	2,16	0,073	0,085
b	1,07	1,33	0,042	0,052
b1	1,90	2,41	0,075	0,095
b2	1,90	2,16	0,075	0,085
b3	2,87	3,38	0,113	0,133
b4	2,87	3,13	0,113	0,123
c	0,55	0,68	0,022	0,027
D	20,80	21,10	0,819	0,831
D1	16,25	17,65	0,640	0,695
D2	0,95	1,35	0,037	0,053
E	15,70	16,13	0,618	0,635
E1	13,10	14,15	0,516	0,557
E2	3,68	5,10	0,145	0,201
E3	1,00	2,60	0,039	0,102
e	5,44 (BSC)		0,214 (BSC)	
N	3		3	
L	19,80	20,32	0,780	0,800
L1	4,10	4,47	0,161	0,176
$\phi P$	3,50	3,70	0,138	0,146
Q	5,49	6,00	0,216	0,236
S	6,04	6,30	0,238	0,248

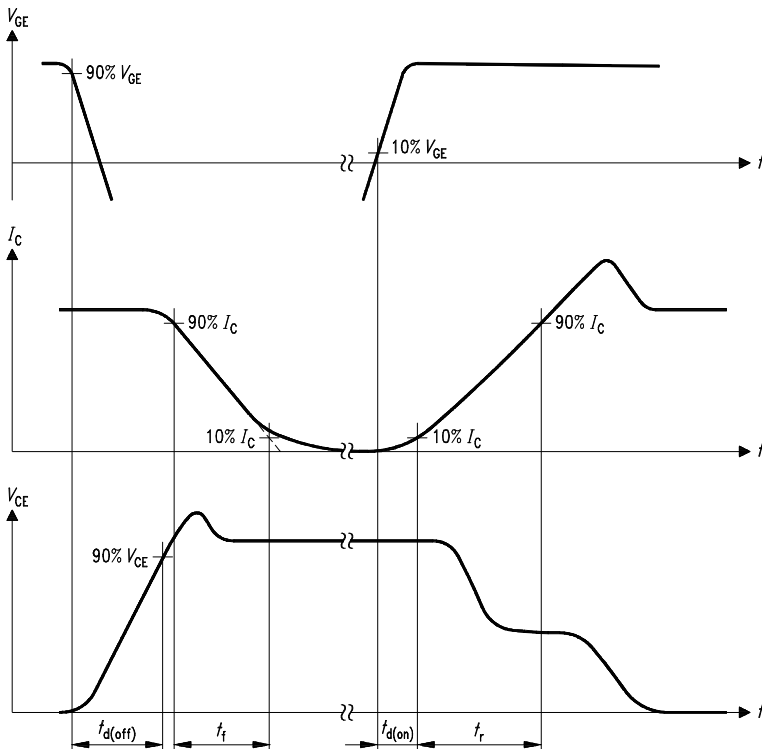
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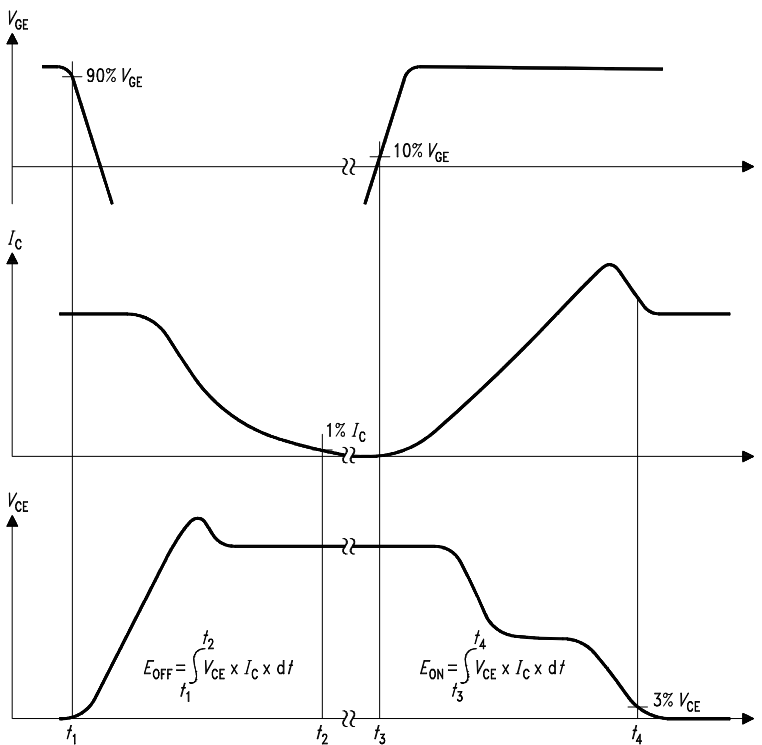
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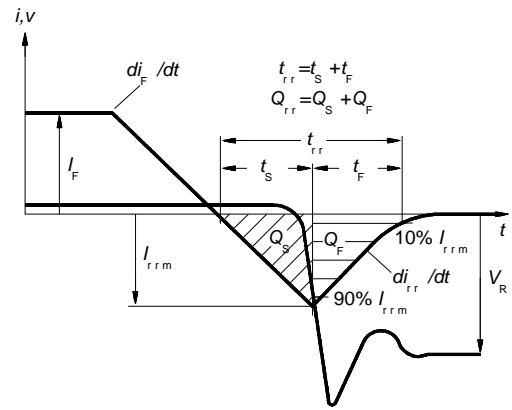
**Figure A. Definition of switching times**

SIS00053

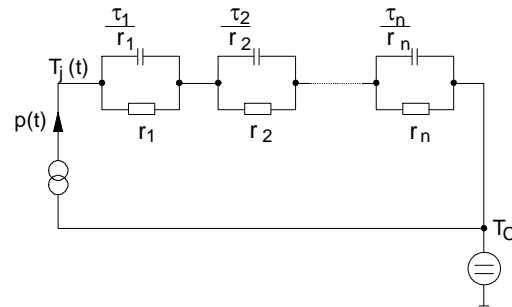


**Figure B. Definition of switching losses**

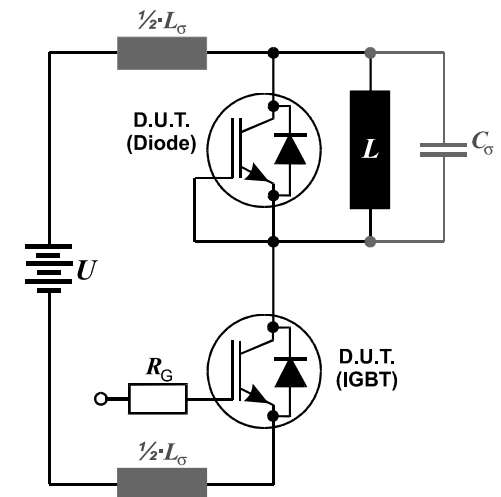
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**Figure C. Definition of diodes switching characteristics**



**Figure D. Thermal equivalent circuit**



**Figure E. Dynamic test circuit**  
Leakage inductance  $L_{\sigma}=180\text{nH}$ ,  
and stray capacity  $C_{\sigma}=40\text{pF}$ .

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